

**ECE2: Physics for Electrical Engineers**  
**Midterm Spring 2019**

May 1st 2019, 2 to 3:55 pm, Franz Hall 1260

**Instructors:** Prof. Chee Wei Wong, Jin Ho Kang and Jiahui Huang  
Closed book, but with 1-sheet (2-sides of 8.5" × 11" paper) of notes.  
Please use calculator.

**Question 1. (30 points) Chapter 1 and 2: The Crystal Structure of Solids & Introduction to Quantum Mechanics**

1.A. (15 points). Determine the wavenumber, wavelength, and period of a wavefunction that describes an electron traveling in free space at a velocity  $v$  of  $5 \times 10^6$  cm/s.

1.B. (15 points). Write down the one-dimensional non-relativistic form of the time-dependent Schrödinger equation. For the one-electron atom wavefunction (hydrogen atom), draw the radial probability density function  $\Psi_{nlm} \Psi_{nlm}^*$  for the principal quantum number  $n = 1$  and  $n = 2$  states.

**Question 2. (35 points) Chapter 3: Introduction to the Quantum Theory of Solids**

2.A. (15 points). The Fermi energy for copper at  $T = 300$  K is 7.0 eV. The electrons in copper follow the Fermi-Dirac distribution function. Find the probability of an energy level at 7.15 eV being occupied by an electron.

2.B. (20 points). Determine the total number ( $\#/cm^3$ ) of energy states in silicon between  $(E_v)$  and  $(E_v - 3kT)$  at  $T = 300$  K.

**Question 3. (35 points) Chapter 4: The Semiconductor in Equilibrium**

3.A. (15 points). In class we taught that the equilibrium electron concentration distribution  $n(E)$  is found from  $n(E) = g(E) f_F(E)$ . Please sketch superimposed plots of  $E$  versus  $g_c(E)$  and  $E$  versus  $f_F(E)$ , and subsequently how the electron and hole concentration distribution are computed? Then please write down how the equilibrium electron concentration can be expressed as a function of the Fermi level and the effective density of states in the conduction band.

3.B. (20 points) Silicon at 300 K is doped with donor impurity atoms at a concentration of  $N_d = 6 \times 10^{15} \text{ cm}^{-3}$ . First, calculate  $(E_c - E_F)$ . Second, calculate the concentration of additional donor impurity atoms that must be added to move the Fermi energy level a distance  $kT$  closer to the conduction band edge.

Helpful constants:

Boltzmann's constant  $k = 1.38 \times 10^{-23} \text{ J/K}$

Planck's constant  $h = 6.625 \times 10^{-34} \text{ J-s}$

Electronic charge  $e = 1.60 \times 10^{-19} \text{ C}$

Electron mass  $m = 9.11 \times 10^{-31} \text{ kg}$